## AMENDMENTS TO THE SPECIFICATION

**At the title page and at page 2, amend the title of the invention:**

~~METHOD AND MATERIAL FOR REMOVING ETCH RESIDUE FROM~~ HIGH ASPECT RATIO CONTACT SURFACES HAVING REDUCED CONTAMINANTS

**At page 2, just before the FIELD OF THE INVENTION section, please add the following new paragraph:**

This application is a divisional of U.S. patent application 10/188,147, filed July 3, 2002, entitled HIGH ASPECT RATIO CONTACT SURFACES HAVING REDUCED CONTAMINANTS, which is a divisional of U.S. patent application 09/653,561, filed August 31, 2000, entitled METHOD AND MATERIAL FOR REMOVING ETCH RESIDUE FROM HIGH ASPECT RATIO CONTACT SURFACES. The entirety of these parent applications are hereby incorporated by reference herein.

**At page 14, second full paragraph (line 10 to line 20):**

Titanium deposition in the contact opening 20 can be done in a manner known in the art. For example, titanium is deposited on the wafer using a sputter process commonly used with metals. A target containing titanium is surrounded by an argon plasma. Ions from the plasma hit the target surface. The titanium atoms which are removed from the metal target then coat the wafer surface. It is also possible to utilize CVD techniques in which the titanium is formed from the reaction of $TiCl_4$ with

hydrogen ($H_2$). In any ~~even~~ event, ~~it is very important that the~~ deposition material should get down into the High Aspect Ratio opening, and reach the bottom surface of the opening or via 20. A collimator may be used to direct the atoms straight down, for better coverage on the contacts.